#### TRI-STATE® 64-Bit Random Access Memories

# **General Description**

The DM76L99/DM86L99 is a fully decoded 64-bit RAM organized as 16 4-bit words. The memory is addressed by applying a binary number to the four Address inputs. After addressing, information may be either written into or read from the memory. To write, both the Memory Enable and the Write Enable inputs must be in the logical "0" state. Information applied to the four Write inputs will then be written into the addressed location. To read information from the memory, the Memory Enable input must be in the logical "0" state and the Write Enable input in the logical "1" state. Information will be read as the complement of what was written into the memory. When the Memory Enable input is in the logical "1" state, the outputs will go to the high-impedance state. This allows up to 75 memories to be connected to a common bus-line without the use of pull-up resistors. All memories except one are gated into the highimpedance state while the one selected memory exhibits the normal totem-pole, low impedance output characteristics of TTL.

#### **Features**

- Same pin-out as SN5489/SN7489, 3101, MM5501
- Organized as 16, 4-bit words
- Expandable to 1200, 4-bit words without additional

■ Typical access from chip enable

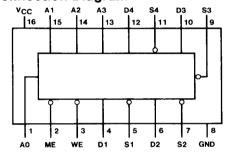
50 ns 80 ns

■ Typical access time

■ Typical power dissipation

75 mW

#### **Connection Diagram**

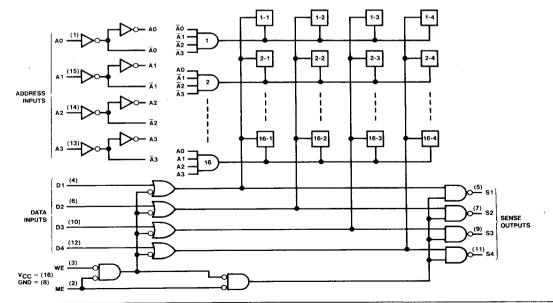


76L99 (J,W); 86L99 (N)

### **Truth Table**

Memory Enable	Write Enable	Operation	Outputs
L	Ļ	Write	Hi-Z
L	Н	Read	Complement of Data Stored in Memory
н	×	Hold	Hi-Z

## **Logic Diagram**





# Electrical Characteristics over recommended operating free-air temperature range (unless otherwise noted)

	Parameter	Conditions		L99			Units
				Min	Typ (1)	Max	1
٧ıH	High Level Input Voltage	V <sub>CC</sub> = Min	2			V	
VIL	Low Level Input Voltage	V <sub>CC</sub> = Min			0.7	V	
VI	Input Clamp Voltage	V <sub>CC</sub> = Min, I <sub>I</sub> = -12			-1.5	V	
ЮН	High Level Output Current				-1.0	mA	
Vон	High Level Output Voltage	VCC = Min, IOH = -	2.4			V	
IOL	Low Level Output Current		DM76L			2.0	mA
			DM86L			3.6	
VOL	Low Level Output Voltage	V <sub>CC</sub> = Min I <sub>OL</sub> = Max	DM76L			0.3	v
			DM86L			0.4	
lO(OFF)		V <sub>CC</sub> = Max	$V_{O} = 0.3 V$			-40	μА
	State) Output Current		$V_0 = 2.4 \text{ V}$			40	
4	Input Current at Maximum Input Voltage	V <sub>CC</sub> = Max, V <sub>I</sub> = 5.5			100	μΑ	
ΙΗ	High Level Input Current	VCC = Max, VI = 2.4			10	μΑ	
IIL	Low Level Input Current	$V_{CC} = Max, V_I = 0.3$			-180	μА	
los	Short Circuit Output Current	V <sub>CC</sub> = Max (2)		-6		-30	mA
lcc	Supply Current	V <sub>CC</sub> = Max		15	19	mA	

Note 1: All typical values are at  $V_{CC} = 5 \text{ V}$ ,  $T_A = 25 ^{\circ}\text{C}$ .

Note 2: Not more than one output should be shorted at a time.

# Switching Characteristics $V_{CC} = 5 V$ , $T_A = 25 ^{\circ}C$

						DM76/86			
Parameter			From	То	Conditions	L99			Units
						Min	Typ (1)	Max	-
<sup>t</sup> PLH	Propagation Low-to-High	Delay Time, Level Output	Address	Output			51	120	ns
<sup>t</sup> PHL	Propagation Delay Time, High-to-Low Level Output		Address	Output	$C_L = 50 \text{ pF, } R_L = 4 \text{ k}\Omega$		77	150	ns
<sup>t</sup> EN	Output Disable Time from Write Enable		WE	Output			73	110	ns
tSR	Sense Recovery Time from Write Enable		WE	Output			110	165	ns
<sup>†</sup> ZH	Output Enabl		ME	Output		-	30	50	ns
<sup>t</sup> ZL	Output Enabl		ME	Output			29	43	ns
tHZ	Output Disable Time from High Level		ME	Output	_		18	27	ns
<sup>t</sup> LZ	Output Disable Time from Low Level		ME	Output	$C_L = 5 pF, R_L = 4 k\Omega$		37	56	ns
tSETUP	Setup Time	Data				0			<del>                                     </del>
		Address				0			ns
9		ME				0			1
†HOLD	Hold Time	Data			, i	0		777.4	ns
		Address				0			
		ME				0			1
twp	VP Write Enable Pulse Width					50	30		ns

